	No.3338	<h1 style="margin: 0;">2SC4475</h1> <p style="margin: 0;">NPN Triple Diffused Planar Silicon Transistor</p> <p style="margin: 0;">High-Voltage Amp, High-Voltage Switching Applications</p>
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**Applications**

- High voltage amp
- High voltage switching
- Dynamic focus

**Features**

- High breakdown voltage ( $V_{CEO \text{ min}} = 1800V$ )
- Small  $c_{ob}$  ( $c_{ob \text{ typ}} = 1.4pF$ )
- Wide ASO
- High reliability (Adoption of HVP process)

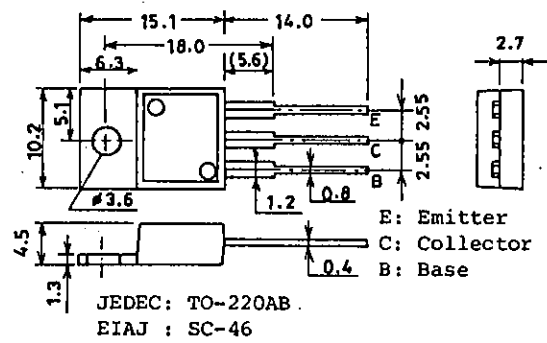
**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

			unit
Collector-to-Base Voltage	$V_{CBO}$	2000	V
Collector-to-Emitter Voltage	$V_{CEO}$	1800	V
Emitter-to-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	3	mA
Peak Collector Current	$i_{cp}$	10	mA
Collector Dissipation	$P_C$	1.75	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

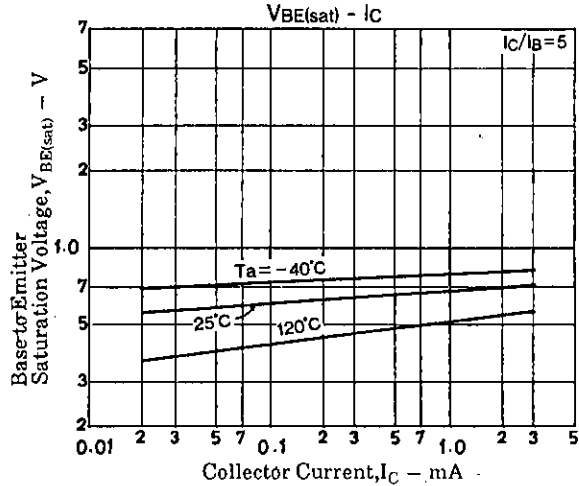
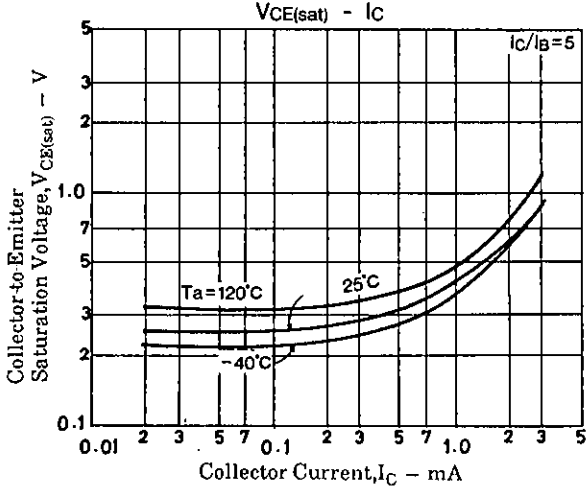
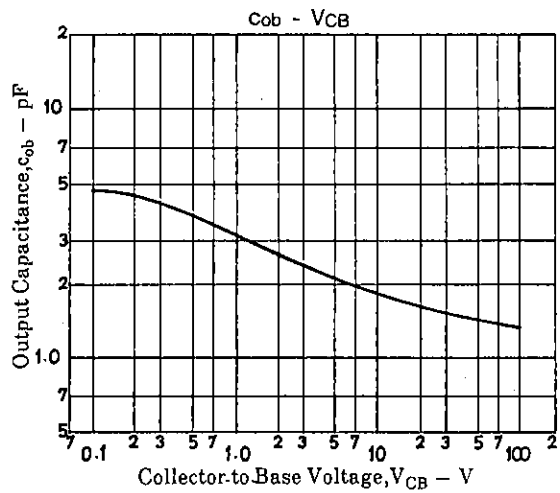
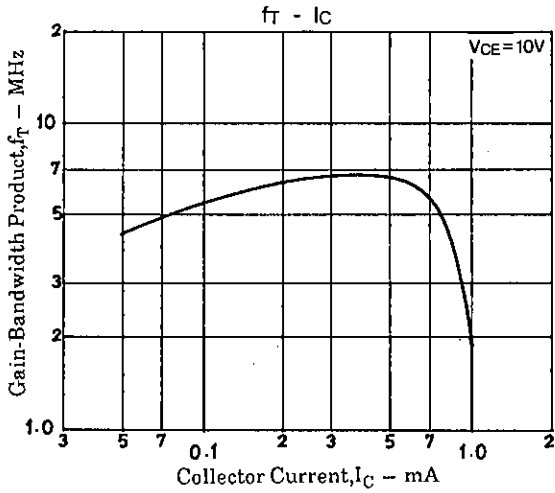
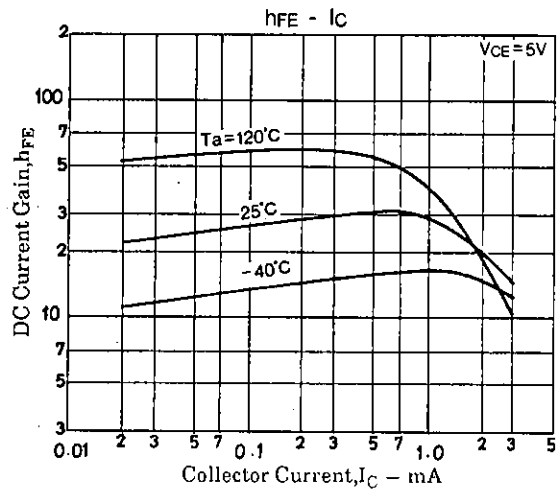
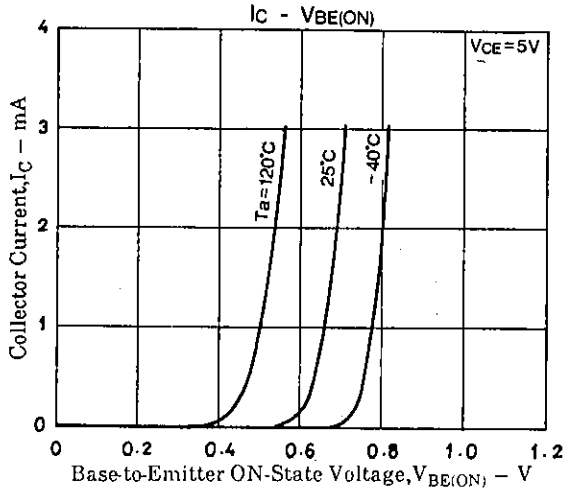
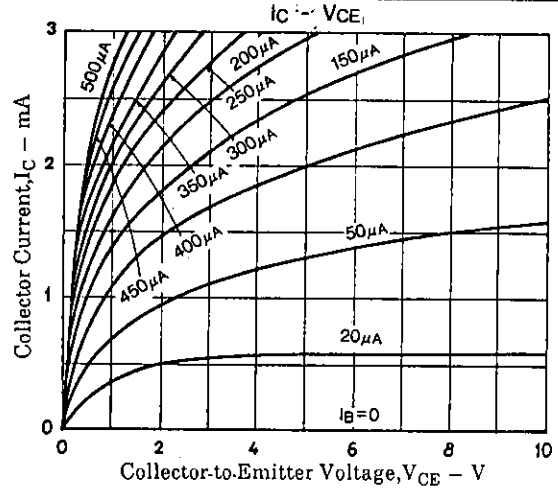
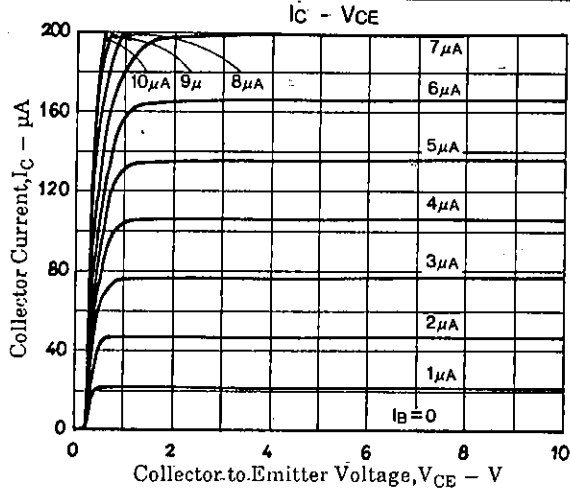
**Electrical Characteristics at  $T_a = 25^\circ C$**

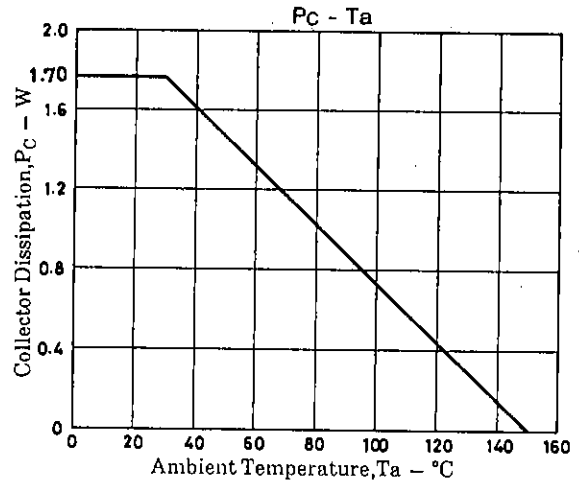
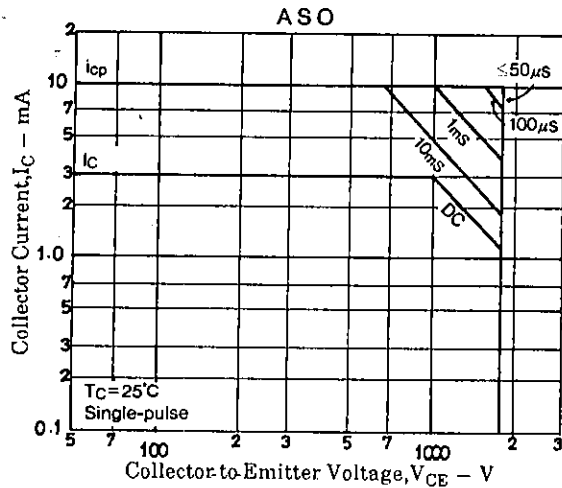
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 1800V, I_E = 0$			1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$			1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 5V, I_C = 100\mu A$	10		60	
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 200\mu A$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 200\mu A, I_B = 40\mu A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 200\mu A, I_B = 40\mu A$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	2000			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu A, R_{BE} = \infty$	1800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Output Capacitance	$c_{ob}$	$V_{CB} = 100V, f = 1MHz$		1.4		pF

**Package Dimensions 2010B**  
(unit: mm)



2SC4475





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